



High-end Power Semiconductor Manufacturer

ZP1000A 1000-1800V Standard Rectifier Diode

- High power cycling capability
- Low on-state and switching losses
- Optimized for line frequency rectifiers
- Designed for traction and industrial applications



Average forward current		I_{FAV}		1000 A	
Repetitive peak reverse voltage		V_{RRM}		1000 – 1800 V	
V_{RRM} , V	1000	1200	1400	1600	1800
Voltage code	10	12	14	16	18
T_j , °C	-60 – 190				

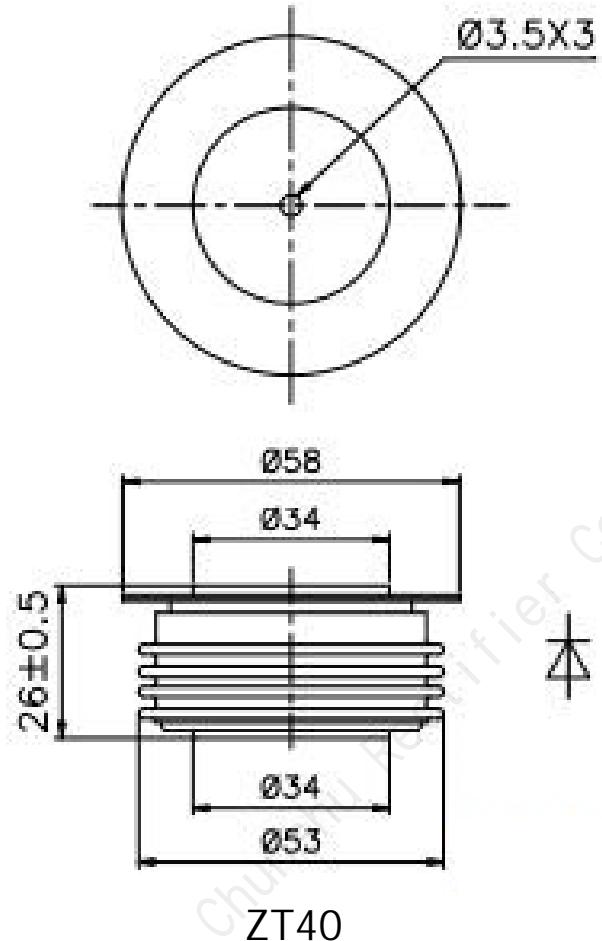
MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions			
ON-STATE							
I_{FAV}	Average forward current	A	1000	$T_c=100$ °C; Double side cooled; 180° half-sine wave; 50 Hz			
I_{FRMS}	RMS forward current	A	1570	$T_c=117$ °C; Double side cooled; 180° half-sine wave; 50 Hz			
I_{FSM}	Surge forward current	kA	16.0	$T_j=T_{j \max}$	180° half-sine wave; 50 Hz ($t_p=10$ ms); single pulse; $V_R=0$ V;		
			18.0	$T_j=25$ °C			
I^2t	Safety factor	$A^2 \cdot 10^3$	17.0	$T_j=T_{j \max}$	180° half-sine wave; 60 Hz ($t_p=8.3$ ms); single pulse; $V_R=0$ V;		
			20.0	$T_j=25$ °C			
			1280	$T_j=T_{j \max}$	180° half-sine wave; 50 Hz ($t_p=10$ ms); single pulse; $V_R=0$ V;		
			1620	$T_j=25$ °C			
			1195	$T_j=T_{j \max}$	180° half-sine wave; 60 Hz ($t_p=8.3$ ms); single pulse; $V_R=0$ V;		
			1660	$T_j=25$ °C			
BLOCKING							
V_{RRM}	Repetitive peak reverse voltages	V	1000–1800	$T_{j \min} < T_j < T_{j \max}$; 180° half-sine wave; 50 Hz;			
V_{RSM}	Non-repetitive peak reverse voltages	V	1100–1900	$T_{j \min} < T_j < T_{j \max}$; 180° half-sine wave; 50 Hz; single pulse;			
V_R	Reverse continuous voltages	V	$0.75 \cdot V_{RRM}$	$T_j=T_{j \max}$;			
THERMAL							
T_{stg}	Storage temperature	°C	-60–190				
T_j	Operating junction temperature	°C	-60–190				
MECHANICAL							
F	Mounting force	kN	9.0–11.0				
a	Acceleration	m/s^2	50 100	Device unclamped Device clamped			

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V _{FM}	Peak forward voltage, max	V	1.56	T _j =25 °C; I _{FM} =3140 A	
V _{F(TO)}	Forward threshold voltage, max	V	0.97	T _j =T _j max;	
r _T	Forward slope resistance, max	mΩ	0.360	0.5 π I _{FAV} < I _T < 1.5 π I _{FAV}	
BLOCKING					
I _{RRM}	Repetitive peak reverse current, max	mA	50	T _j =T _j max; V _R =V _{RRM}	
THERMAL					
R _{thjc}	Thermal resistance, junction to case, max	°C/W	0.040	Direct current	Double side cooled
R _{thjc-A}			0.088		Anode side cooled
R _{thjc-K}			0.072		Cathode side cooled
R _{thck}	Thermal resistance, case to heatsink, max	°C/W	0.008	Direct current	
MECHANICAL					
w	Weight, typ	g	180		
D _s	Surface creepage distance	mm (inch)	23.69 (0.933)		
D _a	Air strike distance	mm (inch)	19.10 (0.752)		

OVERALL DIMENSIONS



All dimensions in millimeters